

#### 60V SELF-PROTECTED LOW-SIDE IntelliFET MOSFET SWITCH

#### **Product Summary**

Continuous Drain-Source Voltage: VDS = 60V

On-State Resistance: 500mΩ

Max Nominal Load Current (V<sub>IN</sub> = 5V): 1.1A

Min Nominal Load Current (V<sub>IN</sub> = 5V): 0.7A

· Clamping Energy: 550mJ

### **Description**

The BSP75NQ-13 is a self-protected low-side IntelliFET® MOSFET. It features monolithic overtemperature, overcurrent, overvoltage (active clamp) and ESD protected logic-level functionality. It is intended as a general-purpose switch.

### **Applications**

- Especially suited for loads with a high in-rush current such as lamps and motors
- All types of resistive, inductive and capacitive loads in switching applications
- µC compatible power switches for 12V and 24V DC applications
- Automotive rated
- Replaces electromechanical relays and discrete circuits
- Linear mode capabilities the current-limiting protection circuitry is designed to de-activate at low V<sub>DS</sub> in order not to compromise the load current during normal operation. The maximum DC operating current is therefore determined by the thermal capability of the package/board combination, rather than by the protection circuitry. This does not compromise the product's ability to self-protect at low V<sub>DS</sub>.





Top View

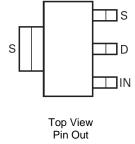
#### **Features and Benefits**

- Short-Circuit Protection with Auto Restart
- Overvoltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Overcurrent Protection
- Input Protection (ESD)
- Load Dump Protection (Actively Protects Load)
- Logic-Level Input
- High Continuous Current Rating
- Lead-Free Finish; RoHS Compliant (Note 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The BSP75NQ-13 is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

#### **Mechanical Data**

- Package: SOT223
- Package Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish @3
- Weight: 0.112 grams (Approximate)



Note: The tab is connected to the source pin and must be electrically isolated from the drain pin. Connection of significant copper to the drain pin is recommended for best thermal performance.

### **Ordering Information** (Note 4)

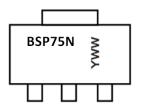
Part Number	Package	Marking	Reel Size (inches)	Tape Width (mm)	Packing	
			Reel Size (Iliches)	rape width (mm)	Qty.	Carrier
BSP75NQ-13	SOT223	BSP75N	13	12	4,000 Units	Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

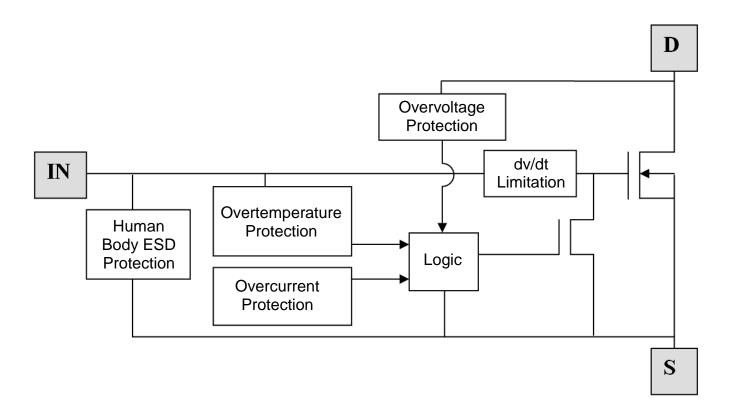


## **Marking Information**



 $\begin{array}{l} {\sf BSP75N} = {\sf Product\ Type\ Marking\ Code} \\ {\sf YWW} = {\sf Date\ Code\ Marking} \\ {\sf Y\ or\ }\overline{{\sf Y}} = {\sf Last\ Digit\ of\ Year\ (ex:\ 4=2024)} \\ {\sf WW\ or\ }\overline{{\sf WW}} = {\sf Week\ Code\ (01\ to\ 53)} \\ \end{array}$ 

# **Functional Block Diagram**





# **Absolute Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Parameter	Symbol	Value	Unit
Continuous Drain-Source Voltage	V <sub>DS</sub>	60	V
Drain-Source Voltage for Short-Circuit Protection, V <sub>IN</sub> = 5V	V <sub>DS</sub> (SC)	36	V
Drain-Source Voltage for Short-Circuit Protection, V <sub>IN</sub> = 10V	V <sub>DS</sub> (SC)	20	V
Continuous Input Voltage	Vin	-0.2 to 10	V
Peak Input Voltage	Vin	-0.2 to 20	V
Operating Temperature Range	TJ	-40 to +150	°C
Storage Temperature Range	Tstg	-55 to +150	°C
Power Dissipation at T <sub>A</sub> = +25°C (Note 5)	P <sub>D</sub>	1.5	W
Power Dissipation at T <sub>A</sub> = +25°C (Note 6)	PD	0.6	W
Continuous Drain Current @ V <sub>IN</sub> = 10V, T <sub>A</sub> = +25°C (Note 5)	ID	1.3	Α
Continuous Drain Current @ V <sub>IN</sub> = 5V, T <sub>A</sub> = +25°C (Note 5)	I <sub>D</sub>	1.1	Α
Continuous Drain Current @ V <sub>IN</sub> = 5V, T <sub>A</sub> = +25°C (Note 6)	I <sub>D</sub>	0.7	А
Continuous Source Current (Body Diode) (Note 5)	Is	2.0	Α
Pulsed Source Current (Body Diode) (Note 7)	Is	3.3	А
Unclamped Single Pulse Inductive Energy	Eas	550	mJ
Load Dump Protection	VLOAD_DUMP	80	V
Electrostatic Discharge (Human Body Model)	Vesd	4000	V
DIN Humidity Category, DIN 40 040	_	E	_
IEC Climatic Category, DIN IEC 68-1	_	40/150/56	_

## **Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction to Ambient (Note 5)	Reja	83	°C/W
Junction to Ambient (Note 7)	Reja	45	°C/W
Junction to Ambient (Note 6)	$R_{\theta JA}$	208	°C/W

Notes:

<sup>5.</sup> For a device surface-mounted on 25mm x 25mm x 1.6mm FR-4 board with a high coverage of single sided 2oz weight copper. Allocation of 6cm<sup>2</sup> copper 33% to source tab and 66% to drain pin with source tab and drain pin electrically isolated.

<sup>6.</sup> For a device surface-mounted on FR-4 board with the minimum copper required for electrical connections.
7. For a device surface-mounted on FR-4 board as (a) and measured at t ≤ 10s.



## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Conditions
Static Characteristics						
Drain-Source Clamp Voltage	VDS(AZ)	60	70	75	V	I <sub>D</sub> = 10mA
Off-State Drain Current	IDSS	_	0.1	3	μA	V <sub>DS</sub> = 12V, V <sub>IN</sub> = 0V
Off-State Drain Current	IDSS	_	3	15	μA	V <sub>DS</sub> = 32V, V <sub>IN</sub> = 0V
Input Threshold Voltage (Note 8)	VIN(TH)	1	2.1	_	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA
Input Current	lın	_	0.7	1.2	mA	VIN = 5V
Input Current	lin	_	1.5	2.7	mA	V <sub>IN</sub> = 7V
Input Current	I <sub>IN</sub>	_	4	7	mA	V <sub>IN</sub> = 10V
Static Drain-Source On-State Resistance	RDS(ON)	_	520	675	mΩ	V <sub>IN</sub> = 5V, I <sub>D</sub> = 0.7A
Static Drain-Source On-State Resistance	RDS(ON)	_	385	550	mΩ	$V_{IN} = 10V, I_D = 0.7A$
Current Limit (Note 9)	I <sub>D(LIM)</sub>	0.7	1.0	1.5	Α	$V_{IN} = 5V$ , $V_{DS} > 5V$
Current Limit (Note 9)	I <sub>D(LIM)</sub>	1	1.8	2.3	Α	V <sub>IN</sub> = 10V, V <sub>DS</sub> > 5V
Dynamic Characteristics						
Turn-On Time (V <sub>IN</sub> to 90% I <sub>D</sub> )	ton	_	3	_	μs	$R_L = 22\Omega$ , $V_{IN} = 0V$ to $10V$ $V_{DD} = 12V$
Turn-Off Time (V <sub>IN</sub> to 90% I <sub>D</sub> )	toff	_	13	_	μs	$R_L = 22\Omega$ , $V_{IN} = 10V$ to $0V$ $V_{DD} = 12V$
Slew Rate On (70% to 50% V <sub>DD</sub> )	-dvps/dton	_	8	_	V/µs	$R_L = 22\Omega$ , $V_{IN} = 0V$ to $10V$ $V_{DD} = 12V$
Slew Rate Off (50% to 70% V <sub>DD</sub> )	dv <sub>DS</sub> /dt <sub>ON</sub>	_	3.2	_	V/µs	$R_L = 22\Omega$ , $V_{IN} = 10V$ to $0V$ $V_{DD} = 12V$
Protection Functions (Note 10)						
Minimum Input Voltage for Overtemperature Protection	VPROT	4.5	_	_	V	_
Thermal Overload Trip Temperature	T <sub>JT</sub>	+150	+175	_	°C	_
Thermal Hysteresis	_	_	+1	_	°C	
Unclamped Single Pulse Inductive Energy T <sub>J</sub> = +25°C	Eas	550	_	_	mJ	$I_{D(ISO)} = 0.7A, V_{DD} = 32V$
Unclamped Single Pulse Inductive Energy T <sub>J</sub> = +150°C	Eas	200	_	_	mJ	I <sub>D</sub> (ISO) = 0.7A, V <sub>DD</sub> = 32V
Inverse Diode						
Source-Drain Voltage	V <sub>SD</sub>	_	_	1	V	$V_{IN} = 0V, -I_D = 1.4A$

Notes:

<sup>8.</sup> Protection features may operate outside spec for  $V_{\text{IN}}$  < 4.5V.

<sup>9.</sup> The drain current is limited to a reduced value when V<sub>DS</sub> exceeds a safe level.
10. Integrated protection functions are designed to prevent IC destruction under fault conditions described in the datasheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous, repetitive operation.



### **Application Information**

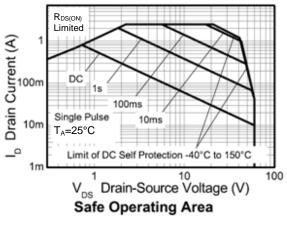
The current-limit protection circuitry is designed to de-activate at low V<sub>DS</sub> to prevent the load current from being unnecessarily restricted during normal operation. The design max DC operating current is therefore determined by the thermal capability of the package/board combination, rather than by the protection circuitry (see *Typical Characteristics* graphs). This does not compromise the products ability to self-protect at low V<sub>DS</sub>.

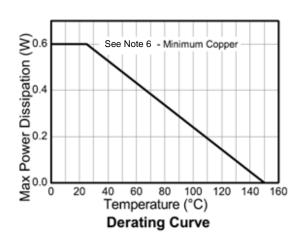
The overtemperature protection circuit trips at a minimum of +150°C. So the available package dissipation reduces as the maximum required ambient temperature increases. This leads to the following maximum recommended continuous operating currents.

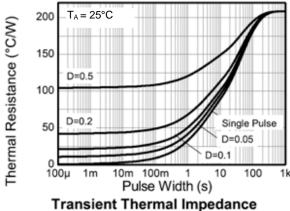
## **Minimum Copper Area Characteristics**

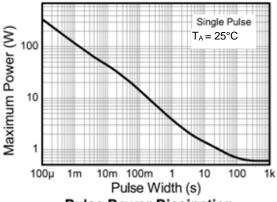
For minimum copper condition as described in Note 6.

May Ambient Temperature T.	Maximum Continuous Current			
Max Ambient Temperature T <sub>A</sub>	VIN = 5V	V <sub>IN</sub> = 10V		
+25°C	720mA	840mA		
+70°C	575mA	670mA		
+85°C	520mA	605mA		
+125°C	320mA	375mA		









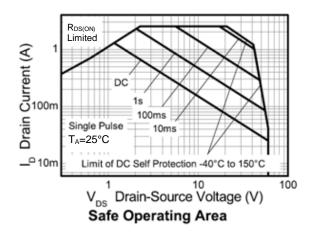
Pulse Power Dissipation

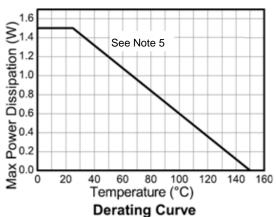


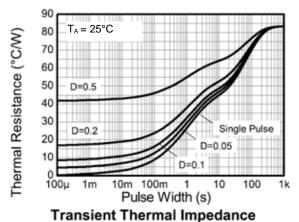
### **Large Copper Area Characteristics**

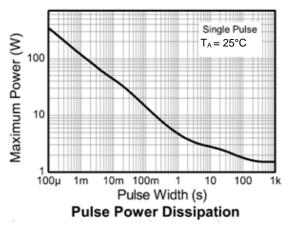
For large copper area as described in Note 5.

May Ambient Temperature T.	Maximum Continuous Current			
Max Ambient Temperature T <sub>A</sub>	V <sub>IN</sub> = 5V	V <sub>IN</sub> = 10V		
+25°C	1140mA	1325mA		
+70°C	915mA	1060mA		
+85°C	825mA	955mA		
+125°C	510mA	590mA		



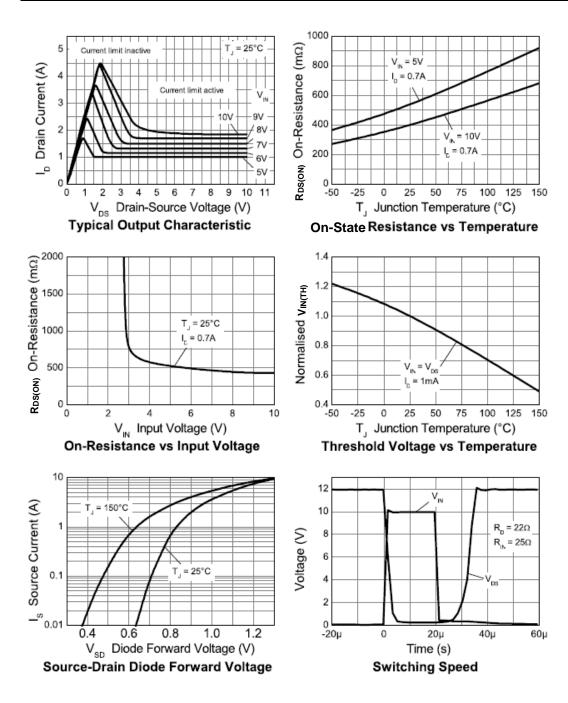








## **Typical Characteristics**

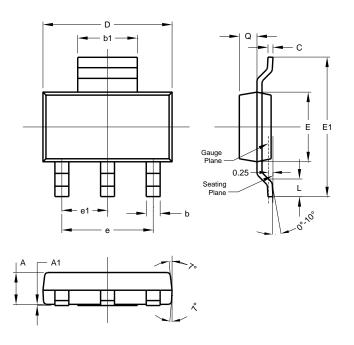




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT223**

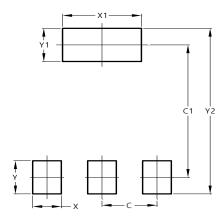


SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b	0.60	0.80	0.70	
b1	2.90	3.10	3.00	
C	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	-	-	4.60	
e1	-	-	2.30	
L	0.85	1.05	0.95	
Ø	0.84	0.94	0.89	
All Dimensions in mm				

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT223**



Dimensions	Value (in mm)	
С	2.30	
C1	6.40	
Х	1.20	
X1	3.30	
Y	1.60	
Y1	1.60	
Y2	8.00	



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